## What Is Claimed Is:

- 1. A control circuit for controlling an electronic circuit, which has a current path through a semiconductor switch (1) and a line; when the semiconductor switch (1) is switched, the inductance of the line and/or of a component in the current path produces an excess voltage between a first and a second current-carrying terminal of the semiconductor switch, wherein the control circuit has a controllable current source (13) for charging or discharging a charge controlled gate of the semiconductor switch (1) with the old of a
  - discharging a charge-controlled gate of the semiconductor switch (1) with the aid of a control current, as well as a control unit (12), the control unit (12) controlling the current source (13) in such a manner, that in the case of a switching operation, the terminal voltage across the current-carrying terminals of the semiconductor switch (1) does not exceed a predefined setpoint terminal voltage (U<sub>DS,setpoint</sub>).
- 2. The control circuit as recited in Claim 1, wherein the setpoint terminal voltage (U<sub>DS,setpoint</sub>) is a function of the maximum permissible terminal voltage between the current-carrying terminals of the semiconductor switch (1).
- 3. The control circuit as recited in Claim 1 or 2, wherein the control unit (12) has a comparator circuit for comparing the terminal voltage (U<sub>DS</sub>) to the setpoint terminal voltage (U<sub>DS,setpoint</sub>) and controlling the current source (13) as a function of the comparison result.
- 4. The control circuit as recited in Claim 3, wherein the control unit (12) has a P controller for controlling the current source (13) in such a manner, that a change in the control current is proportional to the difference between the terminal voltage (U<sub>DS</sub>) and the setpoint terminal voltage (U<sub>DS,setpoint</sub>).
- 5. The control circuit as recited in one of Claims 1 through 4, wherein in a circuit-breaking operation or a circuit-closing operation, the setpoint terminal voltage (U<sub>DS,setpoint</sub>) is greater than the operating voltage applied to the current path.

NY01 1209936 v1 16

- 6. The control circuit as recited in Claim 5, wherein the control input of the semiconductor switch (1) is chargeable via the current source (13) to a potential that is lower than the lowest potential of the current path.
- 7. The control circuit as recited in one of Claims 1 through 6, wherein in a circuit-closing operation, the control unit (12) initially adjusts the setpoint terminal voltage (U<sub>DS,setpoint</sub>) to a first setpoint value, and then to a second setpoint value after expiration of a period of time, the second setpoint value being less than or equal to a low operating potential in the case of a self-blocking semiconductor switch (1), or greater than or equal to a high operating potential in the case of a self-conducting semiconductor switch (1).
- 8. The control circuit as recited in Claim 7, wherein the first setpoint value is selected so that the semiconductor switch (1) operates in its active operating range.
- 9. The control circuit as recited in Claim 7 or 8, wherein a delay element (24) is provided, in order to fix the period of time starting with the circuit-closing operation, the period of time at least corresponding to the time after which the circuit-closing operation is definitely ended.
- 10. The control circuit as recited in Claim 7 or 8, wherein a timing unit is provided for setting the setpoint terminal voltage (U<sub>DS,setpoint</sub>) as a function of a current characteristic and/or voltage characteristic in the current path.
- 11. The control circuit as recited in Claim 10, wherein the semiconductor switch (1) has a field-effect transistor, the terminal voltage representing a drain-source voltage between a drain terminal (D) and a source terminal (S), and the control input representing the gate terminal (G).
- 12. The control circuit as recited in Claim 11, wherein the period of time is determined by the start of a commutation and a maximum commutation period after the start of the circuit-closing operation, the start of commutation being determined in that the increase in the gate-source voltage (U<sub>GS</sub>)

NY01 1209936 v1 17

between the gate terminal (G) and source terminal (S) is 0 for the first time after the start of the circuit-closing operation.

- 13. The control circuit as recited in Claim 11, wherein the period of time is determined by the start of a commutation and a maximum commutation period after the start of the circuit-closing operation, the start of commutation being determined in that the drain-source voltage (U<sub>DS</sub>) falls below a threshold potential, the threshold potential being between a maximum operating potential and the first setpoint voltage.
- 14. The control circuit as recited in Claim 11, wherein the period of time is determined by the start of a commutation and a maximum commutation period after the start of the circuit-closing operation, the start of commutation being determined in that the control current falls below a threshold value for the first time after the start of the circuit-closing operation, the threshold value being between 0 V and a control-current setpoint value.
- 15. The control circuit as recited in one of Claims 1 through 10, wherein the semiconductor switch has an IGBT component.
- 16. A method for controlling an electronic circuit, which has a current path through a semiconductor switch (1) and a line; when the semiconductor switch (1) is switched, the inductance of the line producing an excess voltage between a first and a second current-carrying terminal of the semiconductor switch (1), wherein a gate of the semiconductor switch (1) is charged or discharged with the aid of a control current, the control current being controlled in such a manner that, in the case of a switching operation, the terminal voltage (U<sub>DS</sub>) of the semiconductor switch (1) does not exceed a predefined setpoint terminal voltage (U<sub>DS</sub>, setpoint).

NY01 1209936 v1 18